

Amendments to the Specification:

On page 7, please replace paragraph [0021] with the following amended paragraph.

[0021] As specified in the above, most of tin is able to be fully reacted with the second barrier layer 206d and the wetting layer 206c before reacting with the first barrier layer 206b due to lower concentration of tin, so as to avoid exceeding tin reacting with nickel of the first barrier layer 206b to form discontinuous block at the interface between the first barrier layer 206b and the ~~adhesive~~ wetting layer ~~206a~~ 206c under long-term reaction. Thus, it can enhance the bonding strength of the bumps 208 to the under bump metallization structure 206 and prevent the bumps 208 from peeling off from the under bump metallization structure 206.

On page 7, please replace paragraph [0022] with the following amended paragraph.

[0022] Accordingly, from the above-mentioned, this invention is characterized in that an under bump metallization structure having a tin-copper alloy layer therein taken as another barrier layer is directly formed on the bonding pads of the wafer and connected to the bumps to avoid tin reacting with the first barrier layer 206b and prevent from forming discontinuous blocks, i.e., Ni_3Sn_4 , at the interface between the first barrier layer 206b and the ~~adhesive~~ wetting layer ~~206a~~ 206c under long-term reaction. Thus, it can enhance the bonding strength of the bumps 208 to the under bump metallization structure 206 and prevent the bumps 208 from peeling off from the under bump metallization structure 206.